

BYV34X-600 Dual rectifier diode ultrafast Rev. 01 — 13 September 2007

Product data sheet

1. Product profile

1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT186A (TO-220F)) plastic package.

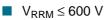
1.2 Features

- Fast switching
- Soft recovery characteristics
- Low forward voltage drop

1.3 Applications

 Output rectifiers in high frequency switched-mode power supplies

1.4 Quick reference data



V_F \le 1.16 V

- Low thermal resistance
- Isolated package
- High thermal cycling performance

 Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

I_{O(AV)} ≤ 20 A
 t_{rr} ≤ 60 ns

2. Pinning information

Table 1. Pinning

	-		
Pin	Description	Simplified outline	Symbol
1	anode 1		
2	cathode	mb	
3	anode 2		
mb	mounting base; isolated		sym084

1 2 3 SOT186A (3-lead TO-220F)



3. Ordering information

Table 2. Ordering information						
Type number	Package	Package				
	Name	Description	Version			
BYV34X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'	SOT186A			

4. Limiting values

Table 3.Limiting values

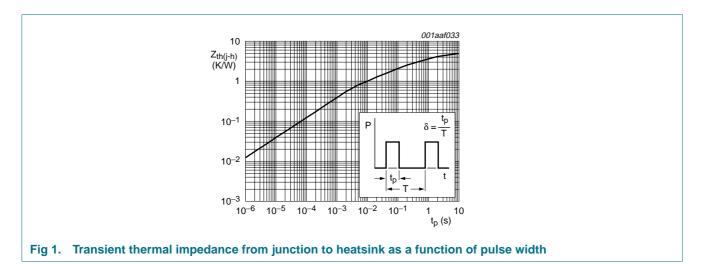
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	square waveform; δ = 1.0; $T_h \leq$ 100 $^\circ C$	-	600	V
I _{O(AV)}	average output current	square waveform; δ = 0.5; T_h \leq 44 °C; both diodes conducting	-	20	А
I _{FRM}	repetitive peak forward current	t = 25 $\mu s;$ square waveform; δ = 0.5; $T_h \leq$ 44 °C; per diode	-	20	A
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform; per diode	-	120	А
		t = 8.3 ms; sinusoidal waveform; per diode	-	132	А
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

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5. Thermal characteristics

Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; per diode; see <u>Figure 1</u>	-	-	5.0	K/W
		with heatsink compound; both diodes conducting	-	-	4.0	K/W
		without heatsink compound; per diode	-	-	7.0	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



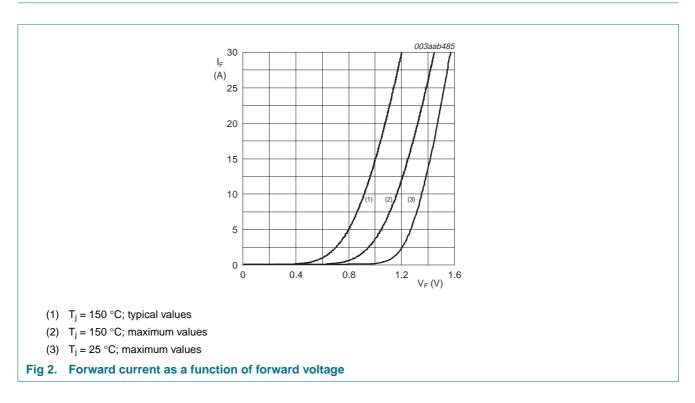
6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \circ C$ unless otherwise specified. Symbol Parameter Conditions Min Unit Тур Max from all terminals to external heatsink; RMS isolation voltage V 2500 Visol(RMS) _ f = 50 Hz to 60 Hz; sinusoidal waveform; relative humidity \leq 65 %; clean and dust free Cisol from cathode to external heatsink; f = 1 MHz isolation capacitance 10 pF --

7. Characteristics

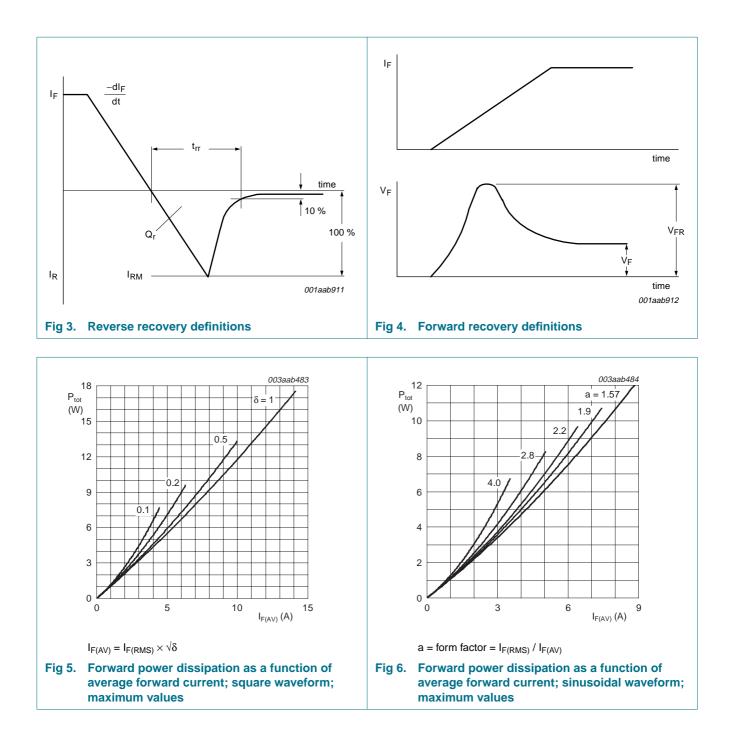
Table 6.Characteristics $T_i = 25 ^{\circ}C$ unless otherwise specified.						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; see <u>Figure 2</u>	-	0.92	1.16	V
		I _F = 10 A; see <u>Figure 2</u>	-	1.07	1.36	V
I _R reverse current		V _R = 600 V	-	10	50	μA
		$V_{R} = 600 \text{ V}; \text{ T}_{j} = 100 ^{\circ}\text{C}$	-	0.2	0.6	mA
Dynamic characteristics						
Qr	recovered charge	I_{F} = 2 A to V_{R} \geq 30 V; dI_{F}/dt = 20 A/µs; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	I_F = 1 A to $V_R \ge$ 30 V; dI_F/dt = 100 A/µs; see Figure 3	-	50	60	ns
I _{RM}	peak reverse recovery current	$ I_F = 10 \text{ A to } V_R \ge 30 \text{ V}; dI_F/dt = 50 A/\mu s; $	-	3	5	A
V _{FR}	forward recovery voltage	$I_F = 10 \text{ A}; \text{ d}I_F/\text{d}t = 10 \text{ A}/\mu\text{s}; \text{ see } \frac{\text{Figure 4}}{10 \text{ A}}$	-	3.2	-	V



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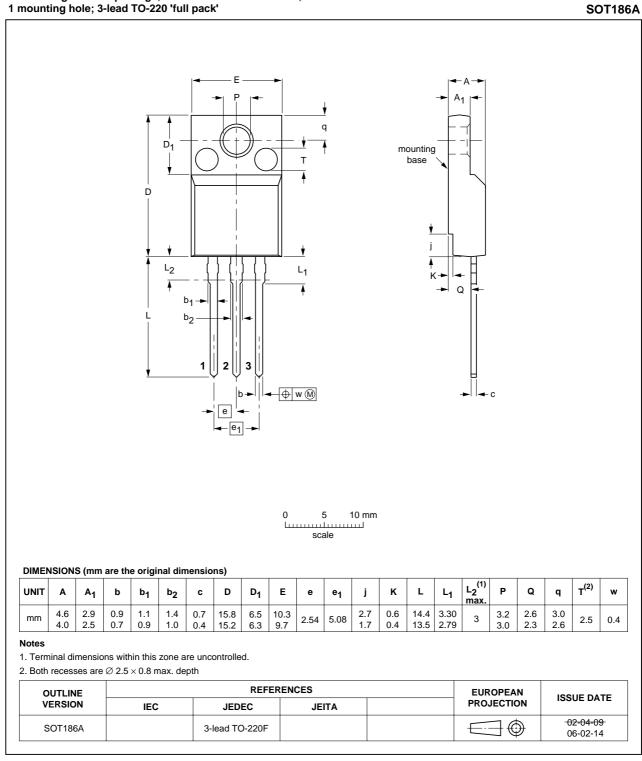
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Package outline 8.



Plastic single-ended package; isolated heatsink mounted;

Fig 7. Package outline SOT186A (3-lead TO-220F)

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9. Revision history

Table 7. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYV34X-600_1	20070913	Product data sheet	-	-	

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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